**Product data sheet** 

# 1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

### 2. Features and benefits

- Fast switching
- · Low reverse recovery current
- Low leakage current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

## 3. Applications

- Half-bridge/full-bridge switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			6	00		V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; $T_{mb} \le$ 130 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		8			А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 130 °C; squarewave pulse	16			А	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	91			А	
		$t_p$ = 8.3 ms; $T_{J(init)}$ = 25 °C; sine-wave pulse			А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
$V_{F}$	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>		-	1.5	1.9	V
Dynamic	characteristics				,		
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	12	18	ns

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**BYC8-600P** 

Hyperfast power diode

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode	] 0 5	K — A 001aaa020
mb	mb	mounting base; connected to cathode	1 2 TO-220AC (SOD59)	001aaa020

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package		Version		
	Name	Description	Version		
BYC8-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

# 7. Marking

### **Table 4. Marking codes**

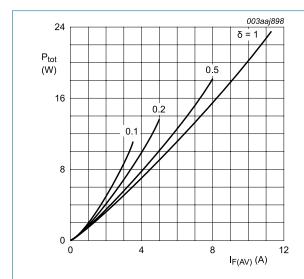
Type number	Marking codes
BYC8-600P	BYC8-600P

# 8. Limiting values

#### **Table 5. Limiting values**

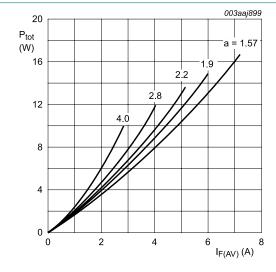
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		600	V
$V_{RWM}$	crest working reverse voltage		600	V
$V_R$	reverse voltage	DC	600	V
I <sub>F(AV)</sub>	average forward current	$δ = 0.5$ ; $T_{mb} \le 130$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	8	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 130 °C; square-wave pulse	16	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	91	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	100	Α
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$  $V_o = 1.581 \text{ V}; R_s = 0.043 \Omega$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$ V<sub>o</sub> = 1.581 V; R<sub>s</sub> = 0.043  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Hyperfast power diode

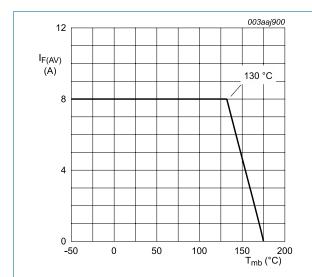


Fig. 3. Average forward current as a function of mounting base temperature; maximum values

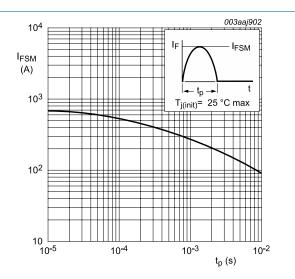


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

Hyperfast power diode

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 5	-	-	2.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

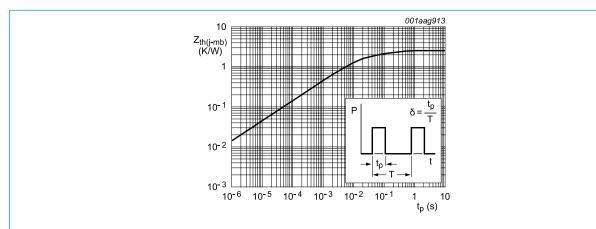
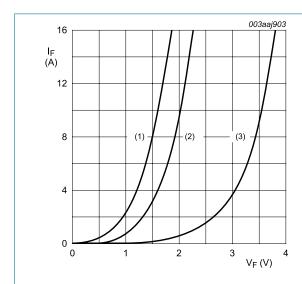


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{F}$	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	-	3.4	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>	-	1.5	1.9	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C	-	1.4	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	20	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C	-	-	200	μA
Dynamic	characteristics					
Q <sub>r</sub>	recovered charge	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu \text{s}; T_J = 25 \text{ °C}; Fig. 7$	-	17	-	nC
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_J = 125 ^{\circ}\text{C}; Fig. 7$	-	90	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	19	-	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	12	18	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	-	2.2	А
		$I_F = 8 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	-	6	А



(1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values (3)  $T_j$  = 25 °C; maximum values

 $V_o$  = 1.581 V;  $R_s$  = 0.043  $\Omega$ 

Fig. 6. Forward current as a function of forward voltage

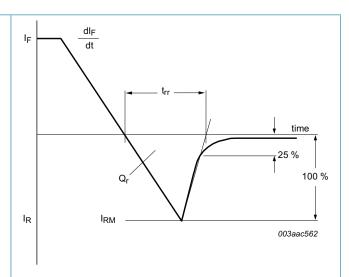
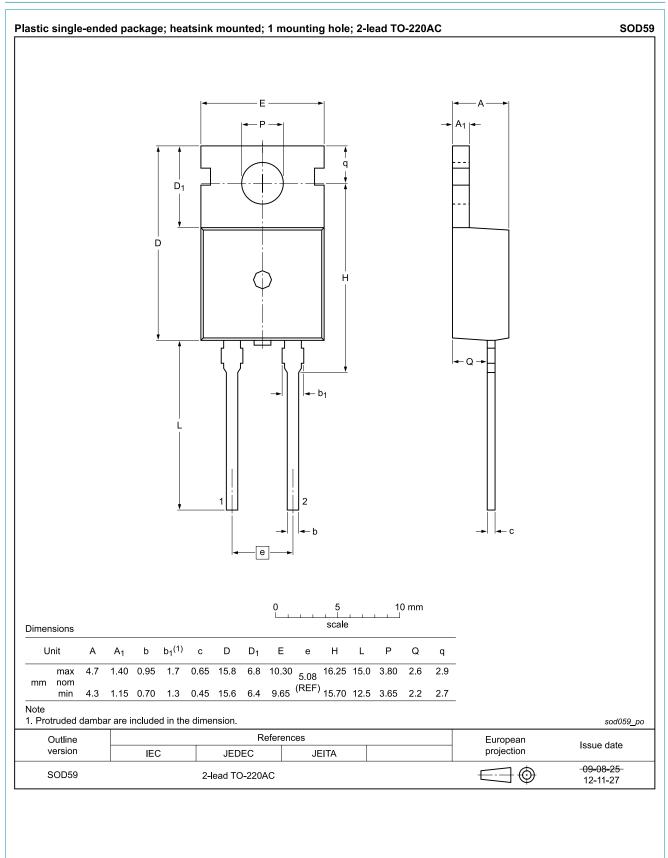


Fig. 7. Reverse recovery definitions; ramp recovery

# 11. Package outline



### Hyperfast power diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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